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VS-2EYH01-M3, VS-2EYH02-M3

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LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS					
I _{F(AV)}	2 A				
V _R	100 V, 200 V				
V _F at I _F	0.69 V				
I _{FSM}	60 A				
t _{rr} (typ.)	15 ns				
T _J max.	175 °C				
Package	SlimSMAW (DO-221AD)				
Circuit configuration	Single				

FEATURES

Hyperfast Rectifier, 2 A FRED Pt[®]

- Low profile package
- · Ideal for automated placement
- · Low forward voltage drop, low power losses
- Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- · Class 2 whisker test
- Compatible to SOD-128 package case outline
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

For use in high frequency, freewheeling, DC/DC converters, PFC, and in snubber industrial, and automotive applications.

MECHANICAL DATA

Case: SlimSMAW (DO-221AD) Molding compound meets UL 94 V-0 flammability rating Halogen-free, RoHS-compliant

Terminals: matte tin plated leads, solderable per J-STD-002

Polarity: color band denotes cathode end

ABSOLUTE MAXIMUM RATINGS						
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Peak repetitive reverse	VS-2EYH01-M3	V		100	V	
voltage VS-2E	VS-2EYH02-M3	V _{RRM}		200	v	
Average rectified forward current		I _{F(AV)} ⁽¹⁾	T _C = 151 °C	2	А	
Non-repetitive peak surge current		I _{FSM}	$T_J = 25 \ ^{\circ}C$, 10 ms sine pulse wave	60		
Operating junction and stor	rage temperatures	T _J , T _{Stg}		-55 to +175	°C	

Note

⁽¹⁾ Mounted on infinite heatsink

ELECTRICAL SPECIFICATIONS ($T_J = 25 \text{ °C}$ unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking VS-2EYH01-M3	V V	L = 100 mA	100	-	-	v	
voltage VS-2EYH02-M3	V _{BR} , V _R	I _R = 100 μA	200	-	-		
Forward voltage, per diade	V _F	I _F = 2 A	-	0.86	0.93		
Forward voltage, per diode		I _F = 2 A, T _J = 150 °C	-	0.69	0.75		
Reverse leakage current, per diode	I _R	$V_{R} = V_{R}$ rated	-	-	2		
neverse leakage current, per diode		$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	-	20	μA	
Junction capacitance	CT	V _R = 200 V	-	12	-	pF	

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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS
		I _F = 1.0 A, dI _F /dt =	50 A/µs, V _R = 30 V	-	22	-	
		I _F = 1.0 A, dI _F /dt =	100 A/ μ s, V _R = 30 V	-	15	-	
Reverse recovery time	t _{rr}	I _F = 0.5 A, I _R = 1A, I _{rr} = 0.25 A		-	-	28	ns
		T _J = 25 °C		-	16	-	
		T _J = 125 °C	I _F = 2 A, dI _F /dt = 200 A/μs, V _B = 100 V	-	26	-	
Book recovery ourrent		T _J = 25 °C		-	2.7	-	A
Peak recovery current	IRRM	T _J = 125 °C		-	3.4	-	
	Q _{rr}	T _J = 25 °C		-	20	-	nC
Reverse recovery charge		T _J = 125 °C		-	43	-	

THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER		SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Maximum junction and stora	ge temperature range	T _J , T _{Stg}		-55	-	175	°C	
Thermal resistance, junction to mount		R _{thJM} ⁽¹⁾	Infinite heatsink	-	12	15		
Thermal resistance, junction to ambient		R _{thJA}	Device mounted on FR4 PCB, 2 oz. standard footprint	-	120	150	°C/W	
VS-2EYH01-M3				2H1				
Marking device	VS-2EYH02-M3	Case style SlimSMAW (DO-221AD)		2H2				

Note

⁽¹⁾ Thermal resistance junction to mount follows JEDEC[®] 51-14 transient dual interface test method (TDIM)

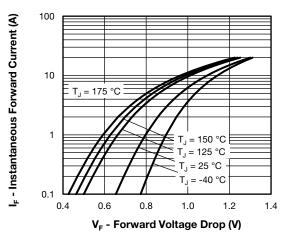


Fig. 1 - Typical Forward Voltage Drop Characteristics

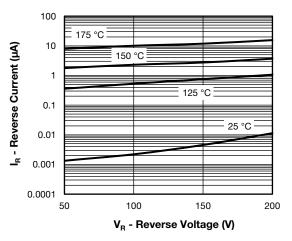


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage



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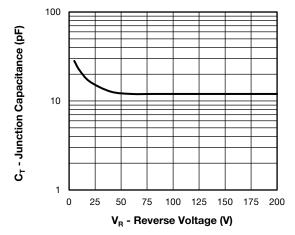


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

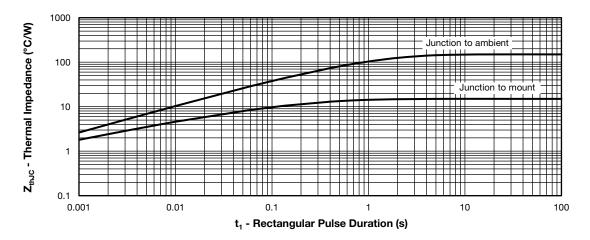
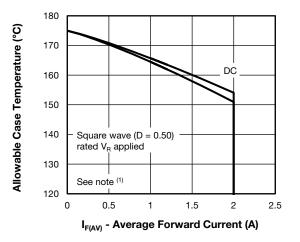
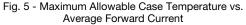


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics





Note

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;

 $\begin{array}{l} \mathsf{Pd} = \mathsf{forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \ \mathsf{x} \ \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{fig.} \ \mathsf{5}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \ \mathsf{x} \ \mathsf{I}_{\mathsf{R}} \ (\mathsf{1} - \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$

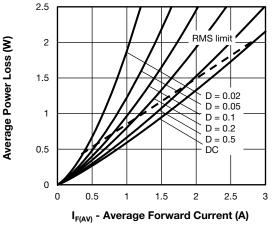


Fig. 6 - Forward Power Loss Characteristics

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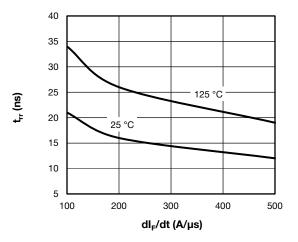
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Fig. 7 - Typical Reverse Recovery Time vs. dI_F/dt

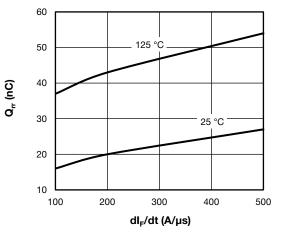


Fig. 8 - Typical Stored Charge vs. dl_F/dt

ORDERING INFORMATION TABLE

Device code	VS-	2	Е	Y	н	02	-	М3	
	1	2	3	4	5	6		7	I
	1 - 2 - 3 -	Cur Circ	rent rati	niconduo ng (2 = : iguration liode	2 A)	oduct			
	4 - 5 -		SlimSM cess typ	IAW (D0 be,	D-221AI	D)			
	6 - 7 -	Volt	age coo	ast recov de (02 = en-free,	200 V)	complia	nt, and	termina	tions lea

ORDERING INFORMATION (Example)									
PREFERRED P/N	UNIT WEIGHT (g)	PREFERRED PACKAGE CODE	BASE QUANTITY	PACKAGING DESCRIPTION					
VS-2EYH01-M3/H	0.033	Н	3500	7"diameter plastic tape and reel					
VS-2EYH01-M3/I	0.033	I	14 000	13"diameter plastic tape and reel					
VS-2EYH02-M3/H	0.033	н	3500	7"diameter plastic tape and reel					
VS-2EYH02-M3/I	0.033	I	14 000	13"diameter plastic tape and reel					

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?96582				
Part marking information	www.vishay.com/doc?95562				
Packaging information	www.vishay.com/doc?88869				
SPICE model	www.vishay.com/doc?96585				

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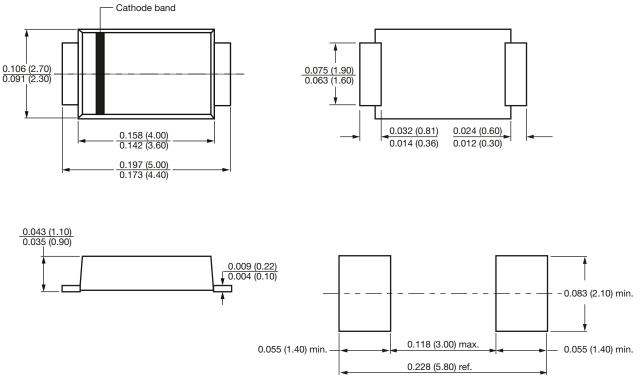
Outline Dimensions

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SlimSMAW (DO-221AD)

DIMENSIONS in inches (millimeters)

SlimSMAW (DO-221AD)



Mounting pad layout





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Revision: 01-Jan-2024